

عنوان مقاله:

Process Optimization of Deposition Conditions for Low Temperature Thin Film Insulators used in Thin Film Transistors Displays

محل انتشار:

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خلاصه مقاله:

Deposition process for thin insulator used in polysilicon gate dielectric of thin film transistors are optimized. Silane and N₂O plasma are used to form SiO₂ layers at temperatures below 150 °C. The deposition conditions as well as system operating parameters such as pressure, temperature, gas flow ratios, total flow rate and plasma power are also studied and their effects are discussed. The physical aspects of the yielded dielectrics such as layer thickness and .uniformity are presented as well

کلمات کلیدی:

Plasma Deposition, Thin Film Transistor, Display, Process Optimization, Low Temperature Dielectric

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